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(54) Title: NON-CONFORMAL HIGH SELECTIVITY FILM FOR ETCH CRITICAL DIMENSION CONTROL

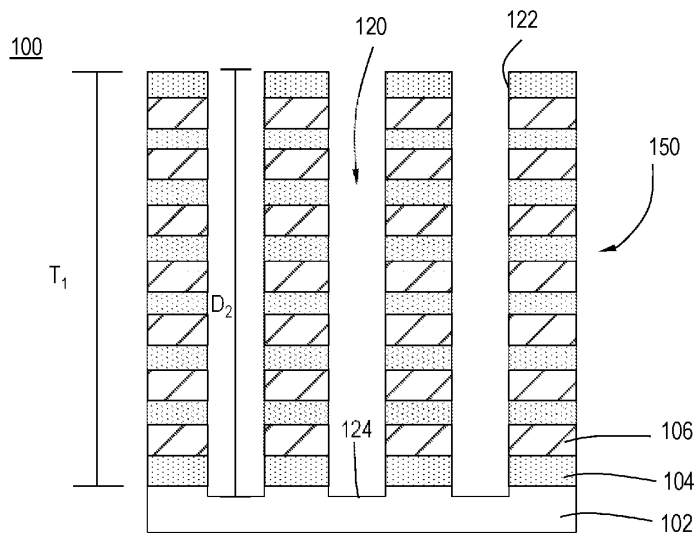


FIG. 9

(57) Abstract: A non-conformal, highly selective liner for etch methods in semiconductor devices is described. A method comprises forming a film stack on a substrate; etching the film stack to form an opening; depositing a non-conformal liner in the opening; etching the non-conformal liner from the bottom of the opening; and selectively etching the film stack relative to the non-conformal liner to form a logic or memory hole. The non-conformal liner comprises one or more of boron, carbon, or nitrogen.

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